L Number	Hits	Search Text	DB	Time stamp
-	50909	substrate and (crystalline or (single adj crystalline) or single-crystalline or monocrystalline or mono-crystalline)	USPAT	2001/10/29 09:14
-	12606	(substrate and (crystalline or (single adj crystalline) or single-crystalline or monocrystalline or mono-crystalline)) and (mask or optical adj mask)	USPAT	2001/10/29 09:14
-	1784	((substrate and (crystalline or (single adj crystalline) or single-crystalline or monocrystalline or mono-crystalline)) and (mask or optical adj mask)) and irradiat$4 and (laser or lasers)	USPAT	2001/10/29 09:16
-	1331	(((substrate and (crystalline or (single adj crystalline) or single-crystalline or monocrystalline or mono-crystalline)) and (mask or optical adj mask)) and irradiat$4 and (laser or lasers)) and (insulati$4 or dielectric)	USPAT	2001/10/29 09:16
-	523	((((substrate and (crystalline or (single adj crystalline) or single-crystalline or monocrystalline or mono-crystalline)) and (mask or optical adj mask)) and irradiat$4 and (laser or lasers)) and (insulati$4 or dielectric)) and (alignment or (alignment adj mark))	USPAT	2001/10/29 09:24
-	381	(((((substrate and (crystalline or (single adj crystalline) or single-crystalline or monocrystalline or mono-crystalline)) and (mask or optical adj mask)) and irradiat$4 and (laser or lasers)) and (insulati$4 or dielectric)) and (alignment or (alignment adj mark))) and amorphous and crystalline	USPAT	2001/10/29 11:41
-	1	("5821562").PN.	USPAT	2001/10/29 11:41
-	1	(("5821562").PN.) and (mask same laser)	USPAT	2001/10/29 11:42
-	1	(("5821562").PN.) and mask and laser	USPAT	2001/10/29 12:50

L Number	Hits	Search Text	DB	Time stamp
-	44910	semiconductor adj substrate	USPAT	2001/10/19 11:50
-	85	(semiconductor adj substrate) and (optical adj mask)	USPAT	2001/10/18 13:48
-	37	((semiconductor adj substrate) and (optical adj mask)) and (insualt$3 or dielectric)	USPAT	2001/10/18 13:49
-	11	(((semiconductor adj substrate) and (optical adj mask)) and (insualt$3 or dielectric)) and (laser or lasers)	USPAT	2001/10/18 14:05
-	224	("438/697").CCLS.	USPAT	2001/10/18 14:08
-	26	(("438/697").CCLS.) and (laser or lasers)	USPAT	2001/10/18 14:12
-	1	((("438/697").CCLS.) and (laser or lasers)) and (optical adj mask)	USPAT	2001/10/18 14:15
-	1	(("438/697").CCLS.) and (laser adj annealing)	USPAT	2001/10/18 14:16
-	1426	laser adj annealing	USPAT	2001/10/18 14:16
-	7	(laser adj annealing) and (optical adj mask)	USPAT	2001/10/18 14:16
-	7	((laser adj annealing) and (optical adj mask)) and (insulat$3 or dielectric)	USPAT	2001/10/18 14:17
-	1486	(laser adj annealing) or (laser adj crystalliz$4)	USPAT	2001/10/19 10:27
-	476	((laser adj annealing) or (laser adj crystalliz$4)) and alignment	USPAT	2001/10/19 10:29
-	419	(((laser adj annealing) or (laser adj crystalliz$4)) and alignment) and (insulating or dielectric)	USPAT	2001/10/19 10:29
-	13	((((laser adj annealing) or (laser adj crystalliz$4)) and alignment) and (insulating or dielectric)) and amorphous and (single adj crystalline) and (monocrystalline)	USPAT	2001/10/19 10:30
-	1	("5643826").PN.	USPAT	2001/10/19 11:50
-	1	(("5643826").PN.) and laser	USPAT	2001/10/19 12:01
-	1	("5620910").PN.	USPAT	2001/10/19 12:01
-	1	(("5620910").PN.) and laser	USPAT	2001/10/19 12:01
-	1	((("5620910").PN.) and laser) and alignment	USPAT	2001/10/19 12:09
-	473	Crystal$ and laser and (alignment adj mark)	USPAT	2001/10/19 12:14
-	23	(Crystal$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)	USPAT	2001/10/19 12:15
-	0	((Crystal$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and ((laser adj anneal) same mask)	USPAT	2001/10/19 12:15
-	0	((Crystal$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and ((laser adj anneal) and mask)	USPAT	2001/10/19 12:15
-	0	((Crystal$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and ((laser adj anneal) and (ARC or mask or resist))	USPAT	2001/10/19 12:16
-	0	((Crystal$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and (laser adj anneal)	USPAT	2001/10/19 12:16

C:\APPS\east\workspaces\09614286.wsp

-	5	((Crystal$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and (laser adj anneal$)	USPAT	2001/10/24 11:02
-	5	((Crystal$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and (laser adj anneal$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/24 11:03
-	5	((Crystal$ and laser and (alignment adj mark)) and (amorphous adj silicon) and (crystalline adj silicon)) and (laser adj anneal$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/24 11:07
-	4527	(thin adj film adj resistor$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/24 11:08
-	94	((thin adj film adj resistor$2)) and amorphous and ((single adj crystalline) or monocrystalline or single-crystalline or crystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/24 11:38
-	16	(("5569610") or ("5543352") or ("0553416") or ("5531182") or ("5529937") or ("5508533") or ("5501989") or ("5488000") or ("5481121") or ("54037722") or ("5289030") or ("5278093") or ("5275851") or ("5147826") or ("4309223") or ("4068020") or ("3783049")).PN.	USPAT	2001/10/24 11:40
-	466	("257/350").CCLS.	USPAT	2001/10/25 15:47
-	305	(("257/350").CCLS.) and ((laser adj anneal) or crystal$ or irradiat$4)	USPAT	2001/10/25 15:49
-	273	(("257/350").CCLS.) and (amorphous or (single-crystalline) or monocrystalline or (single adj crystalline) or crystalline)	USPAT	2001/10/25 15:52
-	104	((("257/350").CCLS.) and ((laser adj anneal) or crystal$ or irradiat$4)) and amorphous and (single-crystalline or monocrystalline or crystalline or (single adj crystalline))	USPAT	2001/10/25 16:11